NIKO-SEM

N-Channel Enhancement Mode Field Effect Transistor

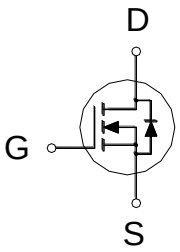
PKCK2BB

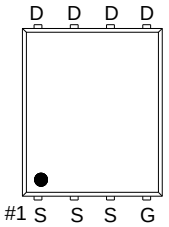
PDFN 5x6P

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	6mΩ	53A





G. GATE
D. DRAIN
S. SOURCE

100% UIS Tested
100% Rg Tested

Features

- Pb−Free, Halogen Free and RoHS compliant.
- Low $R_{DS(on)}$ to Minimize Conduction Losses.
- Ohmic Region Good $R_{DS(on)}$ Ratio.
- Optimized Gate Charge to Minimize Switching Losses.

Applications

- Protection Circuits Applications.
- Computer for DC to DC Converters Applications.

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 °C	I_D	53	A
	T_C = 100 °C		33	
Pulsed Drain Current[1]		I_{DM}	120	
Continuous Drain Current	T_A = 25 °C	I_D	18	
	T_A = 70 °C		15	
Avalanche Current		I_{AS}	25	
Avalanche Energy	L = 0.1mH	E_{AS}	31.2	mJ
Power Dissipation	T_C = 25 °C	P_D	32	W
	T_C = 100 °C		13	
Power Dissipation[3]	T_A = 25 °C	P_D	4.1	W
	T_A = 70 °C		2.6	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	t ≦10s	$R_{\theta JA}$		30	°C / W
Junction-to-Ambient[2]	Steady-State	$R_{\theta JA}$		56	
Junction-to-Case	Steady-State	$R_{\theta JC}$		3.8	

[1]Pulse width limited by maximum junction temperature.
[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.
[3]The Power dissipation is based on $R_{\theta JA}$ t ≦10s value.

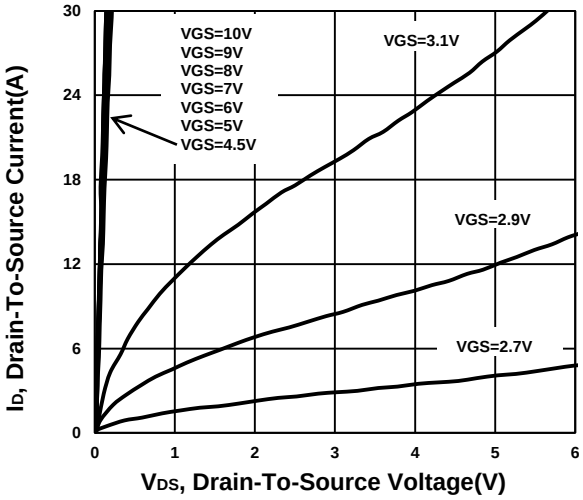
ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS MIN	LIMITS TYP	LIMITS MAX	UNIT
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30			V
Drain-Source Breakdown Voltage (transient)	$V_{(BR)DSSt}$	V_{GS} = 0V, $I_{D(aval)}$ = 12.6A T_{case} = 25 °C , $t_{ransient}$ = 200ns	35			
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.35	1.8	2.3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V			1	μA
		V_{DS} = 20V, V_{GS} = 0V, T_J = 55 °C			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 13A		6	9.5	mΩ
		V_{GS} = 10V, I_D = 13A		4.1	6	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 13A		56		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		918		pF
Output Capacitance	C_{oss}			168		
Reverse Transfer Capacitance	C_{rss}			112		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		1.2		Ω
Total Gate Charge[2]	Q_g (V_{GS} = 10V)	V_{DS} = 15V , V_{GS} = 10V, I_D = 13A		19.3		nC
	Q_g (V_{GS} = 4.5V)			10.4		
Gate-Source Charge[2]	Q_{gs}			2.4		
Gate-Drain Charge[2]	Q_{gd}			5.5		

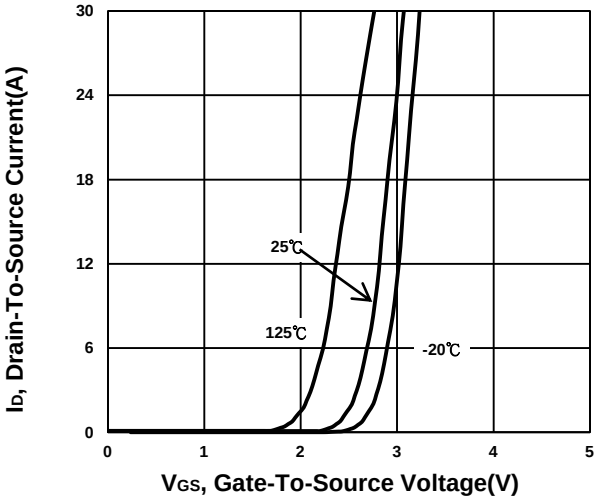
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = 15V , $I_D \cong$ 13A, V_{GS} = 10V, R_{GEN} =6Ω		13		nS
Rise Time[2]	t_r			67		
Turn-Off Delay Time[2]	$t_{d(off)}$			31		
Fall Time[2]	t_f			68		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I_S				26	A
Forward Voltage[1]	V_{SD}	I_F = 13A, V_{GS} = 0V			1.2	V
Reverse Recovery Time	t_{rr}	I_F = 13A, dI_F/dt = 100A / μS		15		nS
Reverse Recovery Charge	Q_{rr}			4.4		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

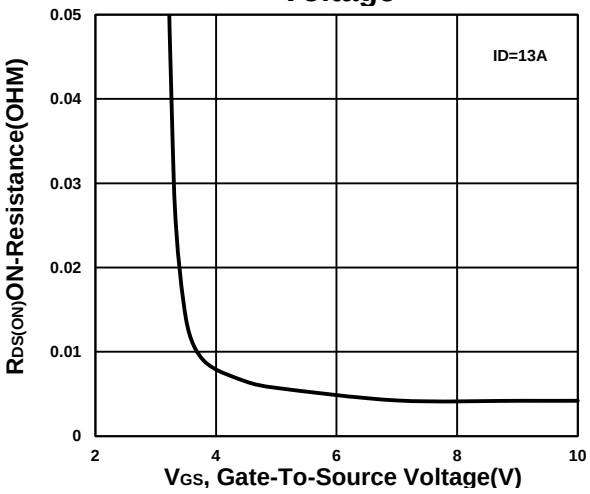
Output Characteristics



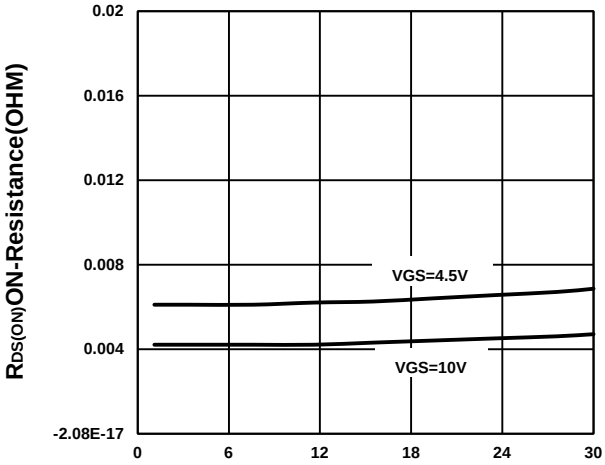
Transfer Characteristics



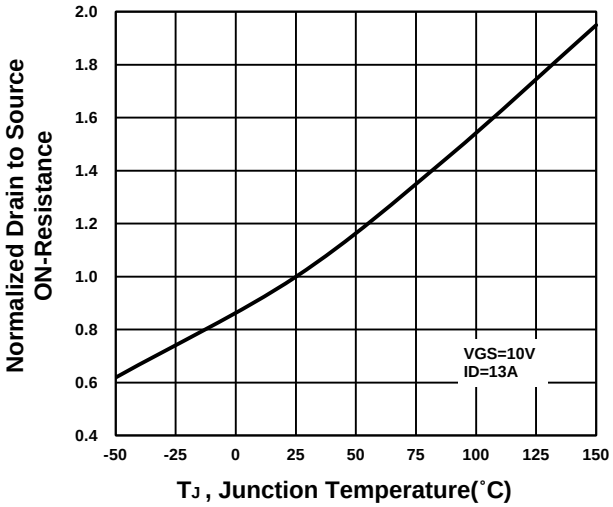
On-Resistance VS Gate-To-Source Voltage



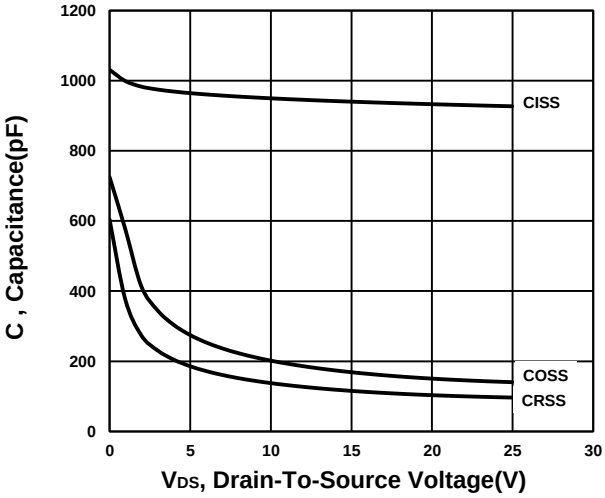
On-Resistance VS Drain Current



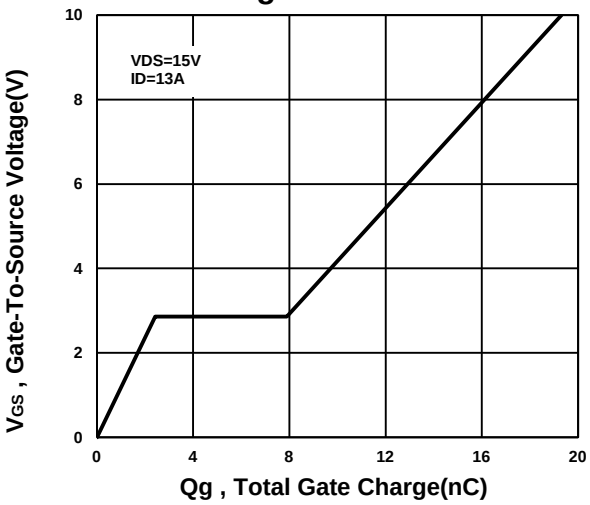
On-Resistance VS Temperature



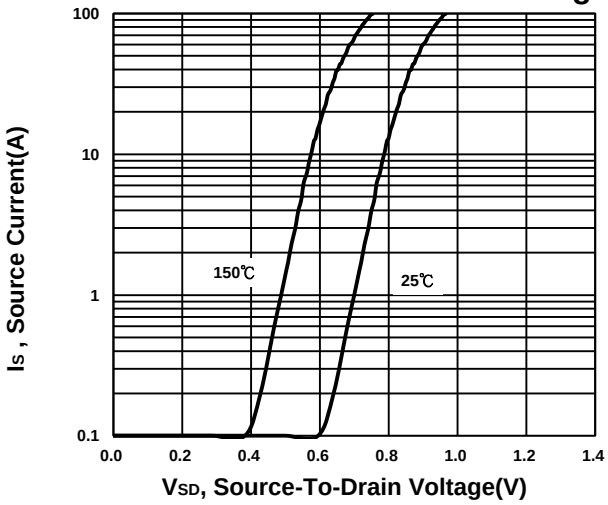
Capacitance Characteristic



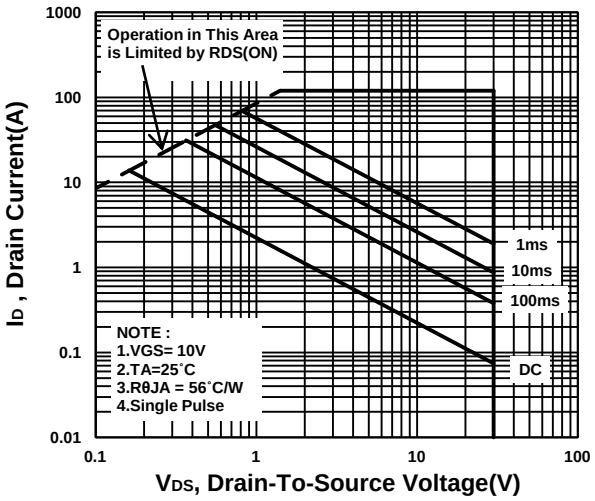
Gate charge Characteristics



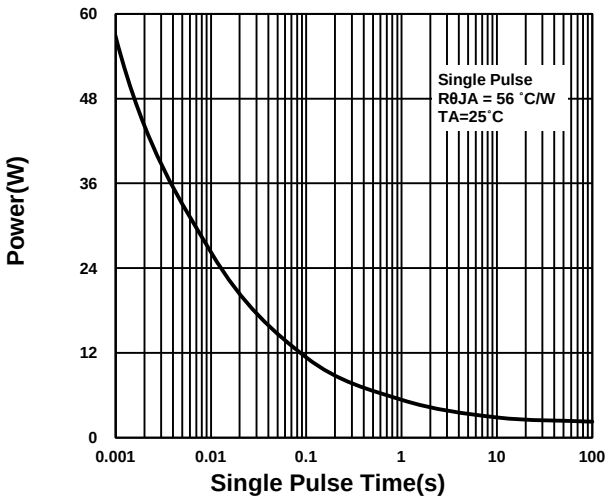
Source-Drain Diode Forward Voltage



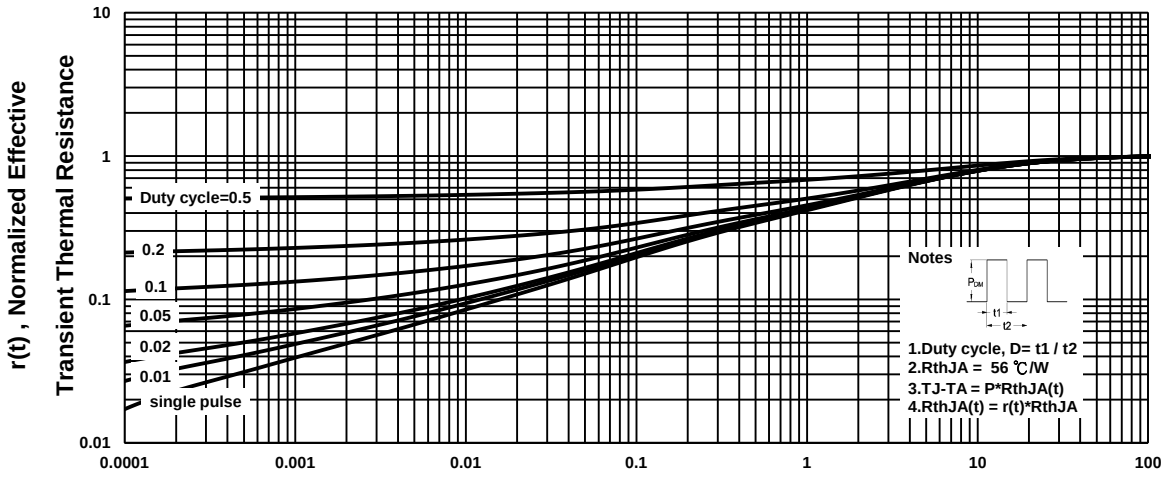
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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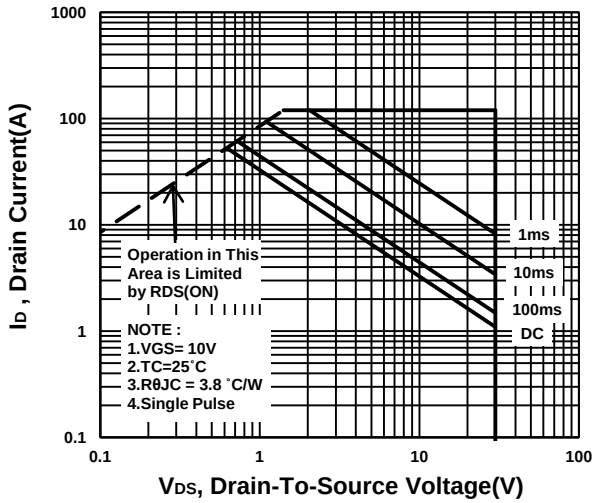
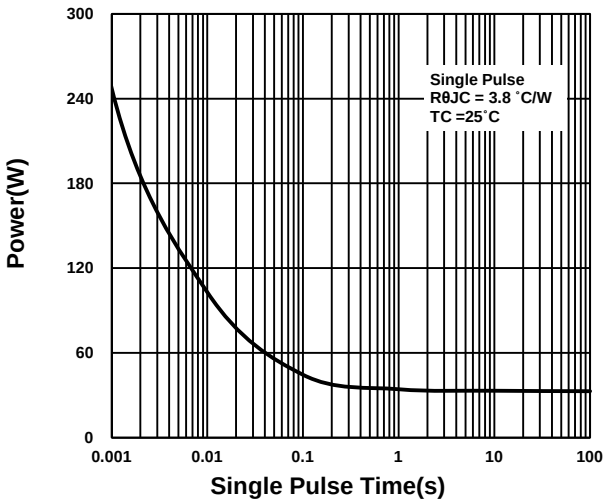


Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve